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## NTE2661 Silicon NPN Transistor Horizontal Deflection Output for HDTV

**Features:**

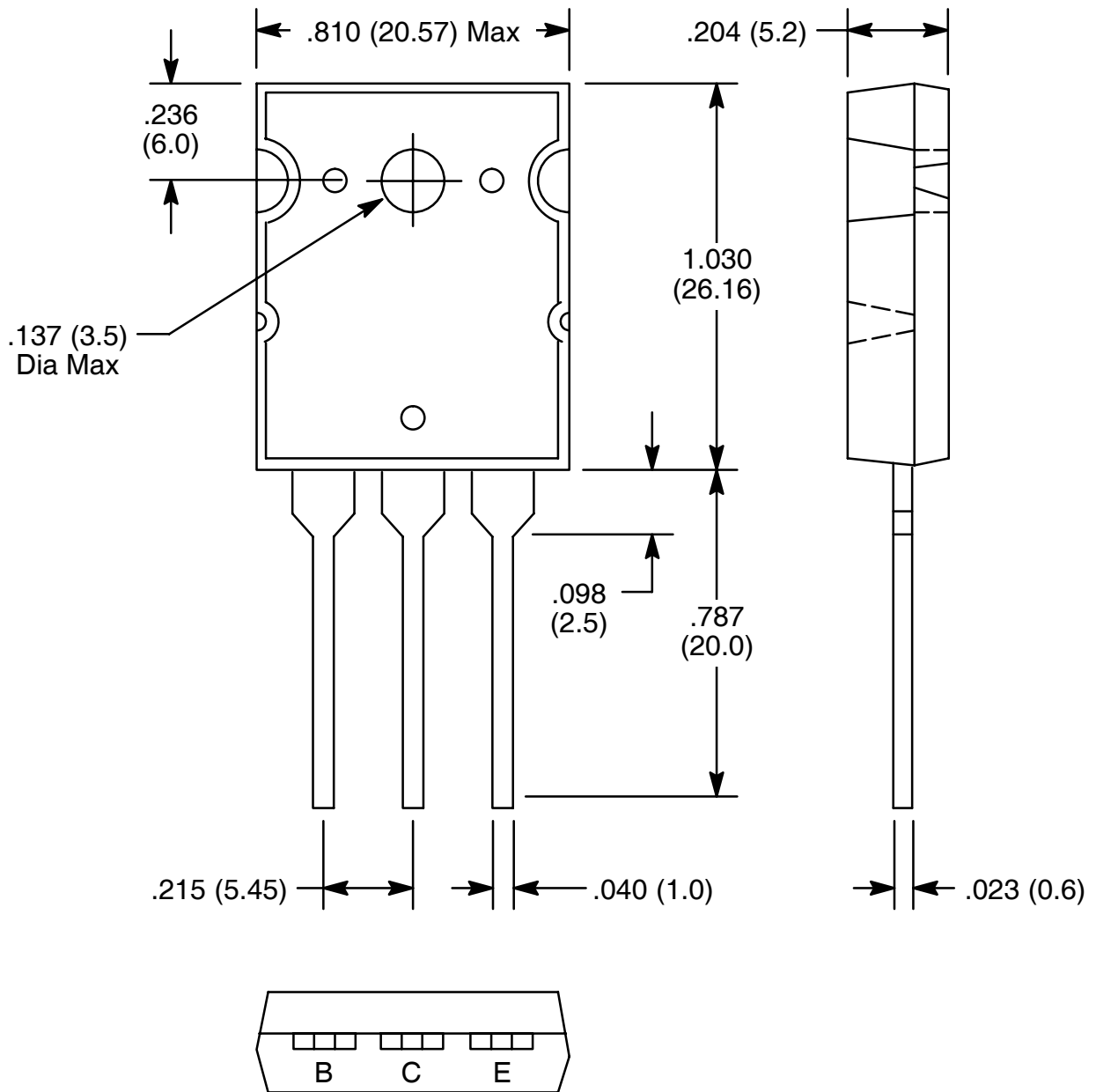
- High Speed:  $t_f = 0.15\mu s$  Typ
- High Breakdown Voltage:  $V_{CBO} = 1700V$
- Low Saturation Voltage:  $V_{CE(sat)} = 3V$  Max

**Absolute Maximum Ratings:** ( $T_A = +25^\circ C$  unless otherwise specified)

Collector-to-Base Voltage, $V_{CBO}$ .....	1700V
Collector-to-Emitter Voltage, $V_{CEO}$ .....	600V
Emitter-to-Base Voltage, $V_{EBO}$ .....	5V
Collector Current, $I_C$	
Continuous .....	20A
Peak .....	40A
Base Current, $I_B$ .....	10A
Collector Power Dissipation ( $T_C = +25^\circ C$ ), $P_C$ .....	200W
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-55° to +150°C

**Electrical Characteristics:** ( $T_A = +25^\circ C$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 1700V, I_E = 0$	-	-	1.0	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5V, I_C = 0$	-	-	10	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 10mA, I_B = 0$	600	-	-	V
DC Current Gain	$h_{FE}$	$V_{CE} = 5V, I_C = 2A$	10	-	30	-
		$V_{CE} = 5V, I_C = 11A$	4.5	-	8.5	-
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 11A, I_B = 2.75A$	-	-	3	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 11A, I_B = 2.75A$	-	1.0	1.3	V
Transition Frequency	$f_T$	$V_{CE} = 10V, I_E = 0.1A$	-	1.7	-	MHz
Collector Output capacitance	$C_{ob}$	$V_{CB} = 10V, I_E = 0, f = 1MHz$	-	290	-	pF
Storage Time	$t_{stg}$	$I_C(\text{peak}) = 10A, I_{B1} = 1.8A, f_H = 64kHz$	-	2.5	4.0	$\mu s$
Fall Time	$t_f$		-	0.15	0.3	$\mu s$



**NOTE:** Pin2 connected to heatsink